

MOSFETs Silicon N-Channel MOS (U-MOSVII-H)

# SSM3K335R

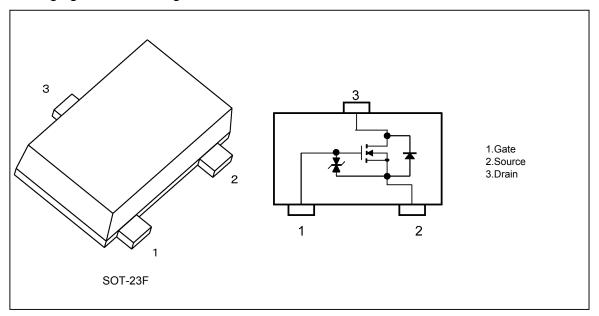
# 1. Applications

- · Power Management Switches
- · DC-DC Converters

#### 2. Features

- (1) 4.5-V gate drive voltage.
- (2) Low drain-source on-resistance
  - $$\begin{split} : R_{DS(ON)} = 38 \text{ m}\Omega \text{ (max) (@V_{GS} = 10 V)} \\ R_{DS(ON)} = 56 \text{ m}\Omega \text{ (max) (@V_{GS} = 4.5 V)} \end{split}$$

#### 3. Packaging and Pin Configuration





# 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25°C)

C	Characteristics	Symbol	Rating	Unit	
Drain-source voltage			V <sub>DSS</sub>	30	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)		(Note 1)	I <sub>D</sub>	6	Α
Drain current (pulsed)		(Note 1,2)	I <sub>DP</sub>	14	
Power dissipation		(Note 3)	P <sub>D</sub>	1	W
Power dissipation	(t ≤ 10 s)	(Note 3)	P <sub>D</sub>	2	W
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%
- Note 3: Device mounted on a FR4 board.(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V	_	_	±10	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	15	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.1 mA	1.3	_	2.5	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 4.0 A, V <sub>GS</sub> = 10 V	_	26	38	mΩ
			$I_D = 2.0 \text{ A}, V_{GS} = 4.5 \text{ V}$		36	56	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5.0 A	13	26	1	S

Note 1: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current  $(I_D)$  to below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 3: Pulse measurement.

## 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V,	Ī	340	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz		20	_	
Output capacitance	C <sub>oss</sub>			60	_	
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = 15 V, $I_{D}$ = 1.0 A $V_{GS}$ = 0 to 4.5 V, $R_{G}$ = 10 $\Omega$ ,	1	14	_	ns
		Duty $\leq$ 1%, Input: $t_r$ , $t_f$ < 5 ns Common source, See Chapter 5.3	ı	12	_	

#### 5.3. Switching Time Test Circuit

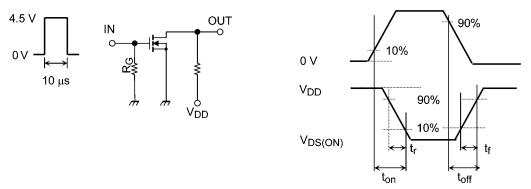


Fig. 5.3.1 Test Circuit of Switching Time

Fig. 5.3.2 Input Waveform/Output Waveform

## 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	V <sub>DD</sub> = 15 V, V <sub>GS</sub> = 4.5 V,	_	2.7	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	$I_D = 6.0 \text{ A}$	_	1.5	_	
Gate-drain charge	$Q_{gd}$		_	0.8	-	



# 5.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = -6.0 A, V <sub>GS</sub> = 0 V	_	-0.87	-1.2	V

Note 1: Pulse measurement.

# 6. Marking

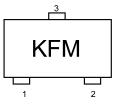


Fig. 6.1 Marking



#### 7. Characteristics Curves (Note)

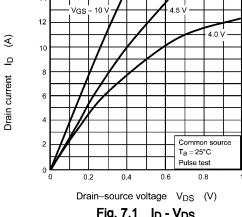
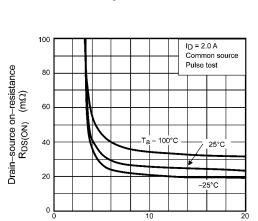
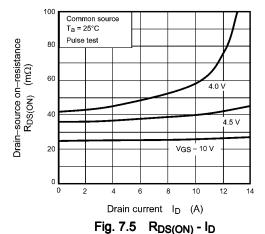


Fig. 7.1 I<sub>D</sub> - V<sub>DS</sub>



Gate-source voltage V<sub>GS</sub> (V) Fig. 7.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>



Pulse test € ٥ Drain current 0. 0.0 0.00 0.0001 Gate-source voltage V<sub>GS</sub> (V) Fig. 7.2 I<sub>D</sub> - V<sub>GS</sub>

Common source

 $V_{DS} = 10 V$ 

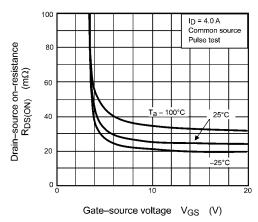


Fig. 7.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

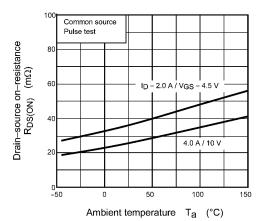
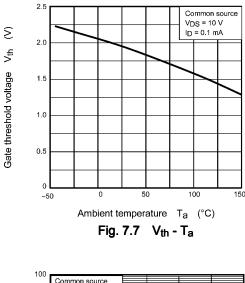


Fig. 7.6 R<sub>DS(ON)</sub> - T<sub>a</sub>



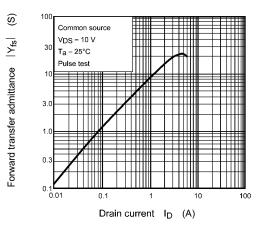


Fig. 7.8 |Y<sub>fs</sub>| - I<sub>D</sub>

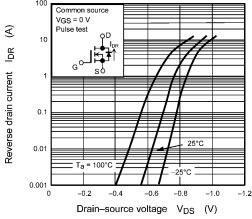
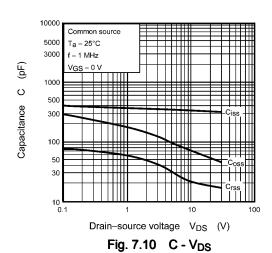
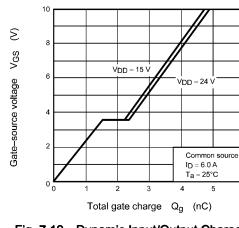


Fig. 7.9  $I_{DR}$  -  $V_{DS}$ 





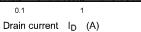


Fig. 7.11 t-I<sub>D</sub>

V<sub>DD</sub> = 15 V V<sub>GS</sub> = 0 to 4.5 V T<sub>a</sub> = 25°C

RG = 10 Ω

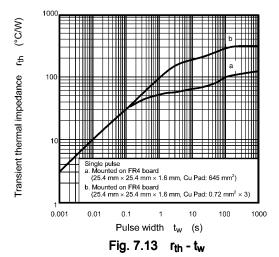
Fig. 7.12 Dynamic Input/Output Characteristics

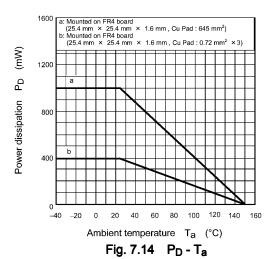
Switching time t (ns)

100

10

0.01





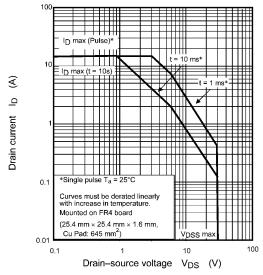


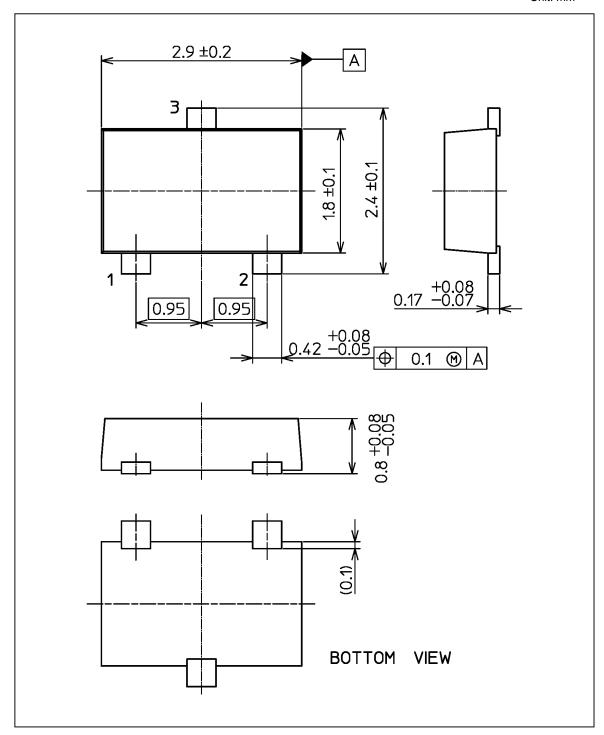
Fig. 7.15 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test.



# **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

Package Nam	e(s)
TOSHIBA: 2-3Z1S	
Nickname: SOT-23F	



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